

ABSTRACT OF DISCLOSURE

In a CMOS image sensor comprising a plurality of unit cells
5 arranged in a matrix array in the vertical and the horizontal
directions to read out a signal from first and second photodiodes
52a, 52b through a common transistor portion, the first and the
second photodiodes are arranged separately to each other in the
vertical direction. The transistor portion comprises a pair of
10 readout transistors, a reset transistor, an amplifying transistor
and a selecting transistor. The pair of the readout transistors
and the reset transistor are located adjacent to a floating
diffusion region of an approximately rectangular shape. Four gate
lines controlling the gates of respective transistors are extended
15 in the horizontal direction of the matrix, and form at least one
double-layered line.